

MSN0340N

V1.4 Datasheet

 $R_{DS(on)} m(\Omega) Max$

 $@V_{GS}=10V$

@V_{GS}=4.5V

N-Channel 40V MOSFET

FEATURES

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

•DC - DC Converter

Motor drivers

Mechanical

●Case:DFN5060 Package

Packing Information

Package	Packing		
DFN5060	3K/13" Reel		

Maximum Ratings (T _A =25°C unless otherwise specified)					
Para	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current 1)3)	T _C =25°C	I _D	110	A	
Continuous Drain Current 1)3)	T _C =100°C	I _D	69	A	
Continuous Drain Current 1)3)	T _c =100°C	I _{DM}	320	A	
Maximum Power Dissipation 1)	P _{tot}	35	W		
Operating Junction and Storage Tem	T _J , T _{STG}	-55 to 175	°C		

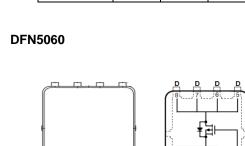
Typical Thermal Resistance				
Parameter	Symbol	Limit	Unit	
Junction-to-Case Thermal Resistance ³⁾	$R_{ extsf{ heta}JC}$	3.5	°C/W	
Junction-to-Ambient Thermal Resistance ³⁾	$R_{\theta JA}$	62.5	°C/W	

Note:

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%

2. Fused current that based on wire numbers and diameter.

Guaranteed by design, not subject to production testing.
The maximum current rating is package limited.
Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keepinitial T_J =25°C.



V_{DS} (V)

40

0

PRODUCTY SUMMARY

2.55

3.5

I_D (A)

110



			IERWISE NOTED) Limits			
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit
		Static			<u> </u>	
Drain-Source Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I _D =250uA	40	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.00	1.40	2.50	V
		V _{GS} =10.0V, I _D =20.0A	-	2.38	2.55	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =20.0A	-	2.8	3.5	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1.0	uA
GateSource Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
		Dynamic ³⁾				
Total Gate Charge	Qg	V_{DS} =20V, V_{GS} =10V, I_{D} =1.0A	-	185	-	nC
Total Gate Charge	Qg		-	91	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =20V, V _{GS} =4.5V, I _D =1.0A	-	15	-	nC
Gate-Drain Charge	Q_{gd}		-	36	-	nC
Input Capacitance	C _{iss}		-	9839	-	pF
Output Capacitance	C _{oss}	V _{DS} =20V, V _{GS} =0V, f=200KHz	-	627	-	pF
Reverse Transfer Capacitance	C _{rss}		-	635	-	pF
		Switching				
Turn-On Delay Time	t _{d(on)}		-	26	-	ns
Turn-On Rise Time	t _r	V_{DS} =20V, R _L =10.0Ω,	-	23	-	ns
Turn-Off Delay Time	t _{d(off)}	V_{GEN} =10V, R _G =3.0 Ω	-	209	-	ns
Turn-Off Fall Time	t _f		-	59	-	ns
	Dra	ain-Source Diode				
Body-Diode Continuous Current	I _S	-	-	-	110	А
Diode Forward Voltage 1)	V _{SD}	I _{SD} =20A, V _{GS} =0V	-	-	1.5	V

Note: 1. Pulse width<300us, Duty cycle<2%.

Essentially independent of operating temperature typical characteristics.

3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_{J} =25°C.

4. The maximum current rating is package limited.

5. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.

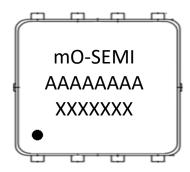
6. Guaranteed by design, not subject to production testing.



Package Outline Dimensions (inches and millimeters)

	D	FN506	60		
Dimensions					
SYMBOL	Millim	neters Inc		hes	
	Min	Max	Min	Max	
А	1.03	1.17	0.041	0.046	
b	0.34	0.48	0.013	0.019	
С	0.82	0.97	0.032	0.038	
D	4.80	5.40	0.189	0.213	
D1	4.11	4.31	0.162	0.170	
D2	4.80	5.00	0.189	0.197	
E	5.95	6.15	0.234	0.242	
E1	5.65	5.85	0.222	0.230	
E2	1.40	-	0.055	-	
E3	1.00	1.20	0.039	0.047	
е	1.27	BSC	0.05	BSC	
L	0.05	0.25	0.002	0.010	
L1	0.38	0.50	0.015	0.020	
L2	0.38	0.71	0.015	0.028	
Н	3.30	3.50	0.130	0.138	
Ι	-	0.18	-	0.007	
Φ	1.10	1.30	0.043	0.051	

Marking Information



First line = Company name

AAAAAAAAA = Product number

XXXXXXX = Tracking number

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